CLAIMS

What is claimed is:

1. A method of forming an interconnection, comprising introducing a barrier material in a via of a dielectric to a circuit device on a substrate in such a manner to deposit the barrier material on the circuit device;

introducing a seed material into said via in a manner that leaves the barrier material overlying the circuit device substantially exposed;

substantially removing the barrier material overlying the circuit device; and

introducing a conductive material in the via to form the interconnection.

2. The method of claim 1, wherein the step of introducing a seed material comprises sputter depositing the seed material into the via.

3. The method of claim 1, wherein the barrier material comprises etch characteristics such that the barrier material may be selectively etched in the presence of the seed material.

4. The method of claim 1, wherein the circuit device is an interconnection line.

5. The method of claim 1, wherein the step of introducing the conductive material comprises electroplating.

6. A method of forming an interconnection on a substrate, comprising:

providing a substrate having a circuit device, a dielectric material overlying the circuit device having a via through the dielectric to the circuit device;

depositing a barrier material in the via to substantially cover the side walls of the via and the circuit device;

introducing a seed material into said via in a manner that leaves the barrier material overlying the circuit device substantially exposed;

substantially removing the barrier material overlying the circuit device; and

introducing a conductive material in the via to form the interconnection.

7. The method of claim 6, wherein the step of introducing a seed material comprises sputter depositing the seed material.

8. The method of claim 7, wherein the step of introducing a seed material comprises introducing the seed material over a portion of a top surface of the dielectric material and an amount of seed material over the barrier material overlying the

circuit device is about five percent or less of the amount overlying the top surface of the dielectric.

9. The method of claim 6, wherein the barrier material comprises etch characteristics such that the barrier material may be selectively etched in the presence of the seed material.

10. The method of claim 6, wherein the circuit device is an interconnection line.

11. The method of claim 6, wherein the step of introducing a conductive material comprises electroplating.

12. An integrated circuit comprising:

a substrate having a circuit device;

a dielectric material overlying the circuit device with a via formed in the dielectric material to the circuit device;

a barrier material substantially lining ~~a wall or walls~~ at least one wall of the via;

a seed layer overlying the barrier material and substantial lining the ~~wall or walls~~ at least one wall of the via; and

a conductive material directly contacting the circuit device.

13. The integrated circuit of claim 10, wherein the circuit device is an interconnection line

14. The integrated circuit of claim 10, wherein the conductive material is copper.